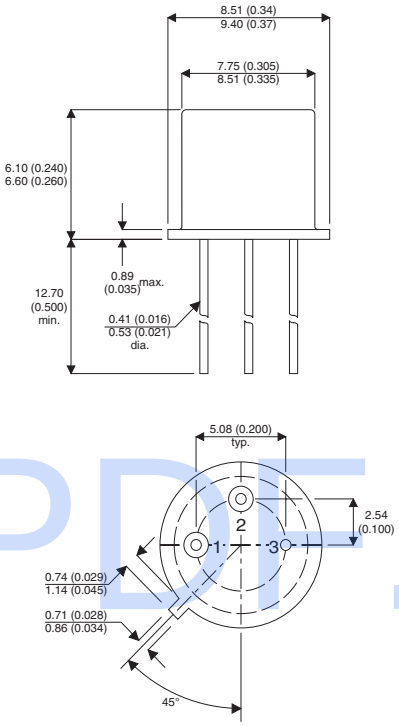
2N4272

MECHANICAL DATA
Dimensions in mm (inches)



TO-39 (TO-205AD) METAL PACKAGE)

Underside View

PIN 1 – Emitter PIN 2 – Base PAD 3 – Collector

BIPOLAR NPN SILICON TRANSISTOR

FEATURES

- **GENERAL PURPOSE NPN TRANSISTOR**
- **HERMETICALLY SEALED METAL PACKAGE**
- **JAN LEVEL SCREENING OPTIONS**
- **CECC LEVEL SCREENING OPTIONS**

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{CBO}	Collector – Base Voltage	180V
V_{CEO}	Collector – Emitter Voltage	140V
V_{EBO}	Emitter – Base Voltage	6V
I_C	Continuous Collector Current	2.5A
P_{tot}	Power Dissipation	10W
$R_{\theta JC}$	Thermal Resistance Junction to Case	15°C/W
T_J, T_{stg}	Operating and Storage Temperature	–55 to 175°C

Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612.
E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk

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SEME LAB

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	I_C = 100μA	I_E = 0	180			V
$V_{(BR)CEO}$	Collector – Emitter Breakdown Voltage	I_C = 10mA	I_B = 0	140			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	I_E = 100μA	I_C = 0	6			
I_{CBO}	Collector – Base Cut-off Current	V_{CB} = 175V	I_E = 0			100	μA
I_{CEO}	Collector – Emitter Cut-off Current	V_{CE} = 10V	I_B = 0			10	mA
$V_{CE(sat)}$	Collector – Emitter Saturation Voltage	I_C = 500mA	I_B = 50mA			0.6	V
V_{BE}	Base – Emitter Voltage	I_C = 1A	V_{CE} = 10V			1.1	
h_{FE}	Static Forward Current Transfer Ratio	I_C = 1A	V_{CE} = 10V	20		140	—

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